

General Description

- Trench Power MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

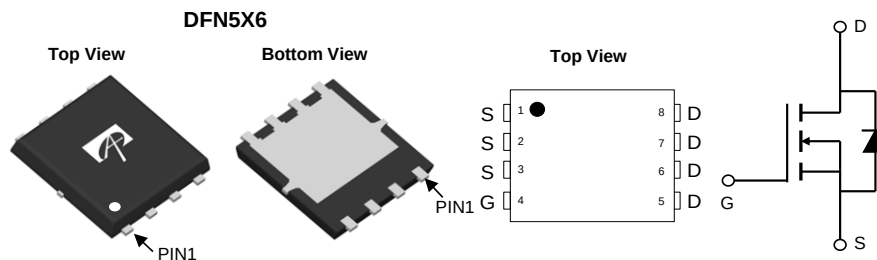
Applications

- Motor, Oring, Efuse
- High current battery charge/discharge

Product Summary

V_{DS}	30V
I_D (at $V_{GS}=10V$)	220A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 1.35m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 1.9m Ω

100% UIS Tested
100% Rg Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AONS32311	DFN 5x6	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ^G	I _D	220	A
Continuous Drain Current ^G	I _D	140	
Pulsed Drain Current ^C (≤10μs)	I _{DM}	880	
Continuous Drain Current	I _{DSM}	56	A
Continuous Drain Current	I _{DSM}	45	
Avalanche Current ^C	I _{AS}	70	A
Avalanche energy L=0.1mH ^C	E _{AS}	245	mJ
Power Dissipation ^B	P _D	119	W
Power Dissipation ^B	P _D	48	
Power Dissipation ^A	P _{DSM}	6.2	W
Power Dissipation ^A	P _{DSM}	4.0	
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	t ≤ 10s	R _{θJA}	15	20	°C/W
Maximum Junction-to-Ambient ^{A,D}	Steady-State		40	50	°C/W
Maximum Junction-to-Case	Steady-State	R _{θJC}	0.85	1.05	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.3	1.8	2.3	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		1.1 1.75	1.35 2.2	mΩ
		V _{GS} =4.5V, I _D =20A		1.5	1.9	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		143		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.66	1	V
I _S	Maximum Body-Diode Continuous Current				140	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		6060		pF
C _{oss}	Output Capacitance			710		pF
C _{rss}	Reverse Transfer Capacitance			550		pF
R _g	Gate resistance	f=1MHz	0.4	0.8	1.2	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =20A		110	150	nC
Q _g (4.5V)	Total Gate Charge			54		nC
Q _{gs}	Gate Source Charge			16.5		nC
Q _{gd}	Gate Drain Charge			25		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		13		ns
t _r	Turn-On Rise Time			11		ns
t _{D(off)}	Turn-Off DelayTime			78		ns
t _f	Turn-Off Fall Time			18		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=500A/μs		16		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=500A/μs		40		nC

- A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.
- G. The maximum current rating is package limited.
- H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

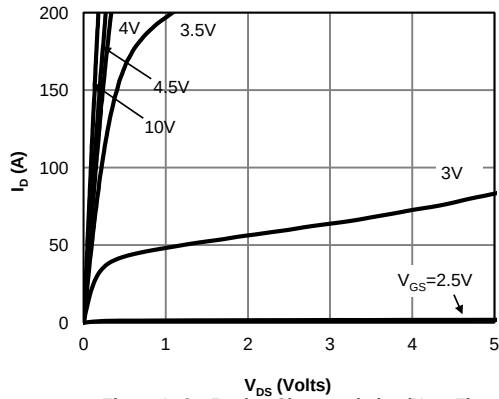


Figure 1: On-Region Characteristics (Note E)

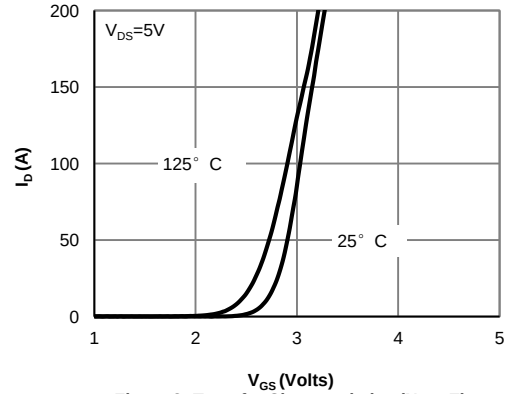


Figure 2: Transfer Characteristics (Note E)

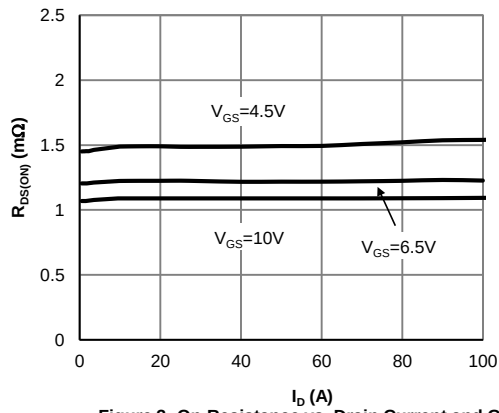


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

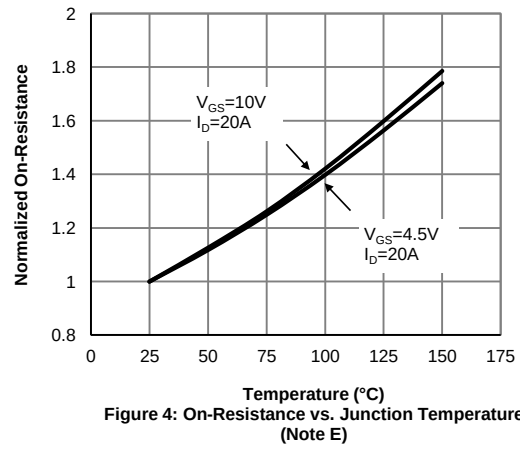


Figure 4: On-Resistance vs. Junction Temperature (Note E)

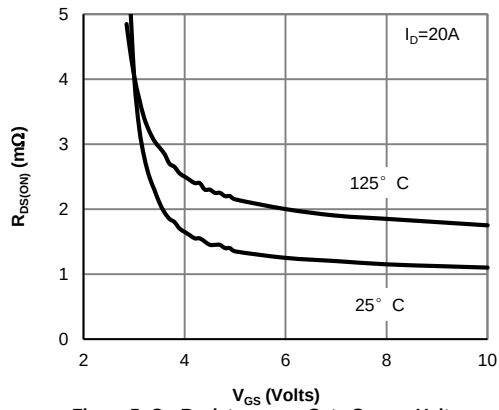


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

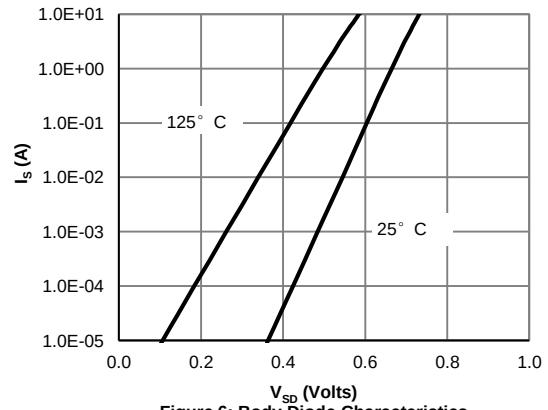
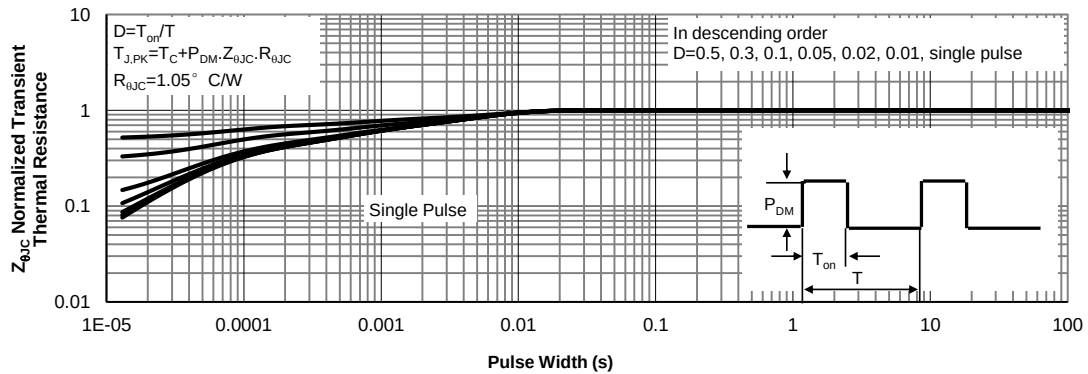
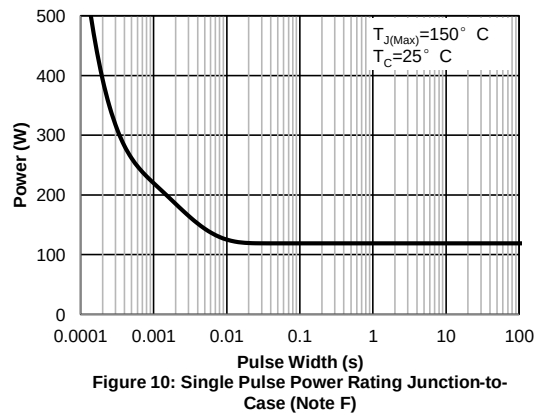
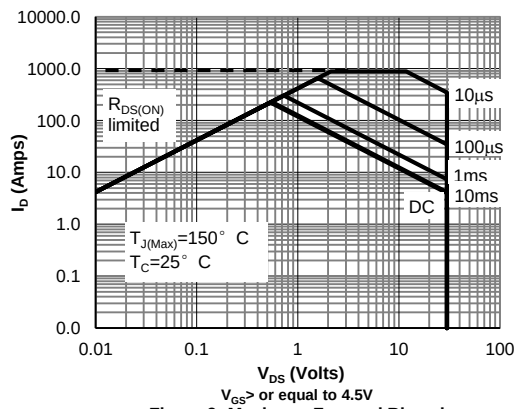
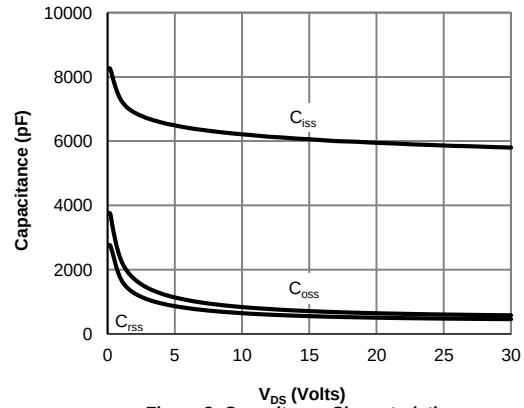
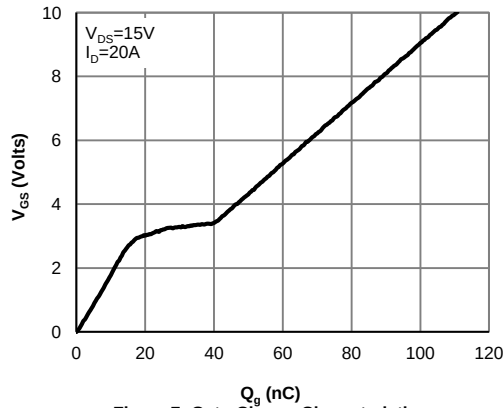


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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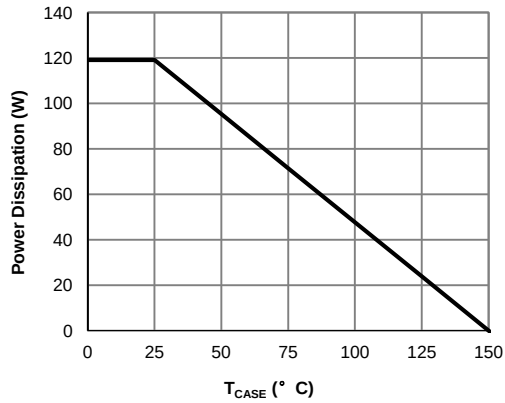


Figure 12: Power De-rating (Note F)

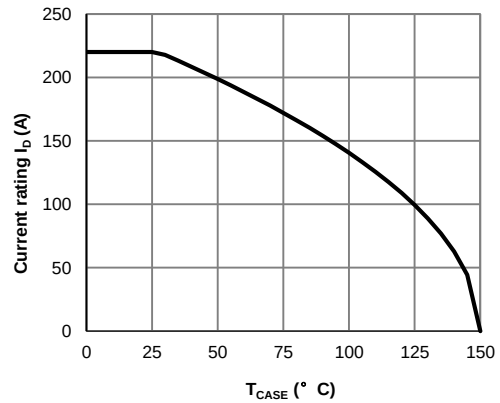


Figure 13: Current De-rating (Note F)

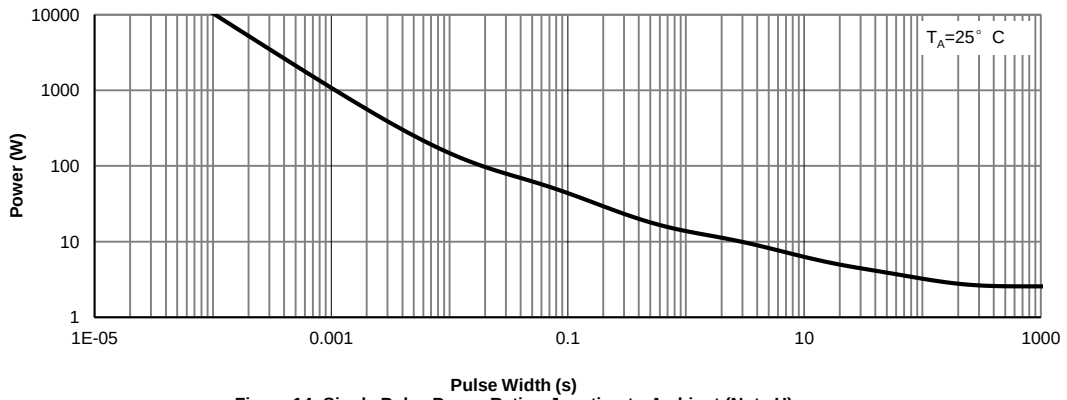


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

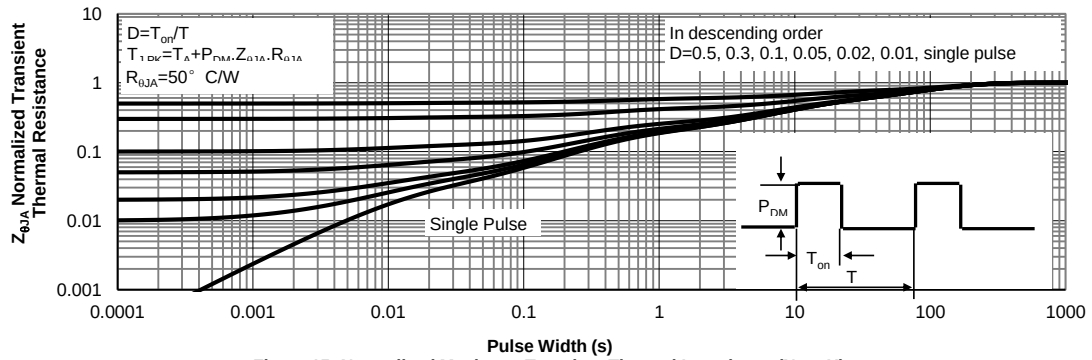


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

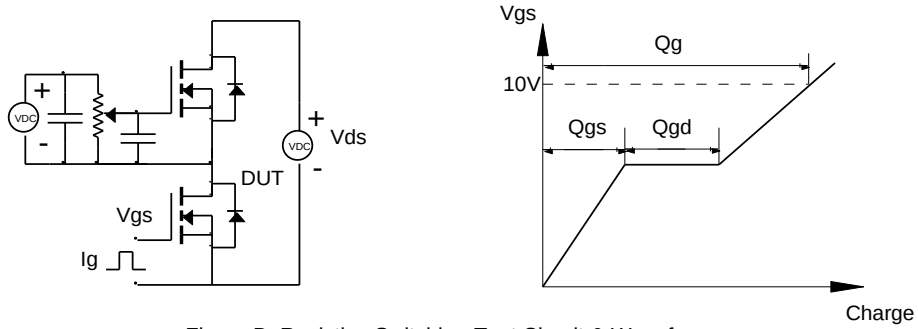


Figure B: Resistive Switching Test Circuit & Waveforms

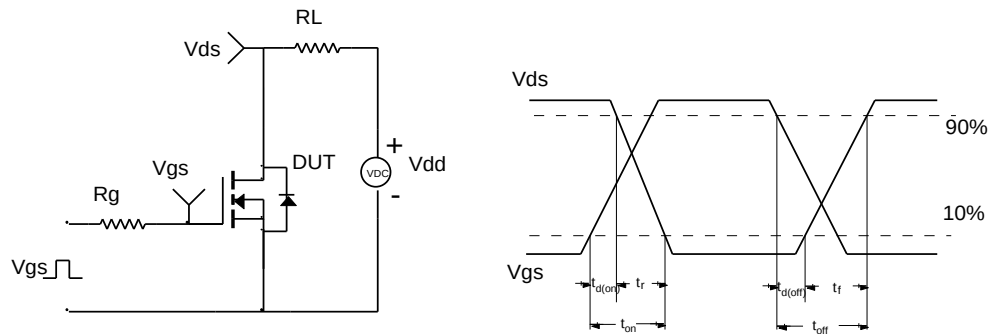


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

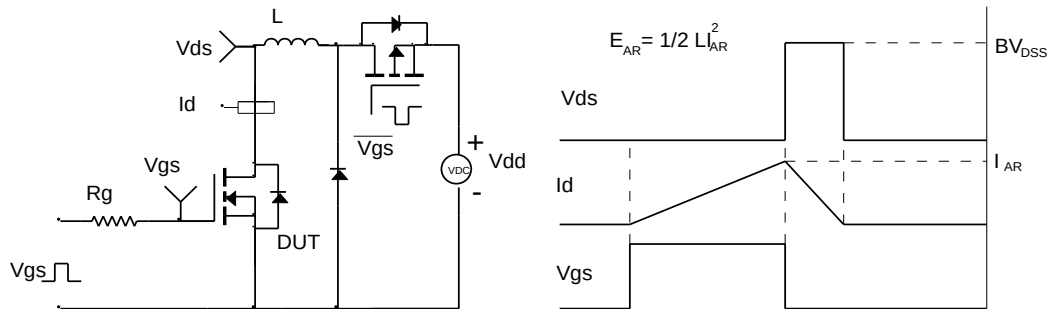


Figure D: Diode Recovery Test Circuit & Waveforms

